

VII and VIII International Conferences on Physics and Technology of Nanoheterostructure Microwave Electronics: Mokerov Readings 2016 & Mokerov Readings 2017

IOP Conference Series: Materials Science and Engineering
Volume 475

Moscow, Russia
25 May 2016 and 24 May 2017

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ISBN: 978-1-5108-8218-8
ISSN: 1757-8981

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Readings 2017**

25 May 2016, Moscow, Russian Federation

Accepted papers received: 21 December 2018

Published online: 18 February 2019

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